

Thyristors

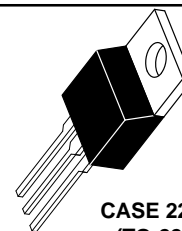
Silicon Controlled Rectifiers

... designed for back-to-back SCR output devices for solid state relays or applications requiring high surge operation.

- Photo Glass Passivated Blocking Junctions for High Temperature Stability, Center Gate for Uniform Parameters
- 400 Amperes Surge Capability
- Blocking Voltage to 800 Volts

**MCR264-4
thru
MCR264-10**

**SCRs
40 AMPERES RMS
200 thru 800 VOLTS**



**CASE 221A-04
(TO-220AB)
STYLE 3**

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted.)

Rating	Symbol	Value	Unit
Peak Repetitive Forward and Reverse Blocking Voltage ⁽¹⁾ (T _J = 25 to 125°C, Gate Open)	V _{DRM} V _{RRM}	200 400 600 800	Volts
Forward Current (T _C = 80°C) (All Conduction Angles)	I _{T(RMS)} I _{T(AV)}	40 25	Amps
Peak Non-repetitive Surge Current – 8.3 ms (1/2 Cycle, Sine Wave) 1.5 ms	I _{TSM}	400 450	Amps
Forward Peak Gate Power	P _{GM}	20	Watts
Forward Average Gate Power	P _{G(AV)}	0.5	Watt
Forward Peak Gate Current (300 μs, 120 PPS)	I _{GM}	2	Amps
Operating Junction Temperature Range	T _J	–40 to +125	°C
Storage Temperature Range	T _{stg}	–40 to +150	°C

1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

These devices are rated for use in applications subject to high surge conditions. Care must be taken to insure proper heat sinking when the device is to be used at high sustained currents.

REV 1

MCR264-4 thru MCR264-10

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1	$^{\circ}C/W$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	60	$^{\circ}C/W$

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
Peak Forward or Reverse Blocking Current ($V_{AK} = \text{Rated } V_{DRM} \text{ or } V_{RRM}$, Gate Open) $T_J = 25^{\circ}C$ $T_J = 125^{\circ}C$	I_{DRM}, I_{RRM}	— —	— —	10 2	μA mA
Forward "On" Voltage ⁽¹⁾ ($I_{TM} = 80 A$)	V_{TM}	—	1.4	2	Volts
Gate Trigger Current (Continuous dc) (Anode Voltage = 12 Vdc, $R_L = 100 \text{ Ohms}$, $T_C = -40^{\circ}C$)	I_{GT}	— —	15 30	50 90	mA
Gate Trigger Voltage (Continuous dc) (Anode Voltage = 12 Vdc, $R_L = 100 \text{ Ohms}$)	V_{GT}	—	1	1.5	Volts
Gate Non-Trigger Voltage (Anode Voltage = Rated V_{DRM} , $R_L = 100 \text{ Ohms}$, $T_J = 125^{\circ}C$)	V_{GD}	0.2	—	—	Volts
Holding Current (Anode Voltage = 12 Vdc)	I_H	—	30	60	mA
Turn-On Time ($I_{TM} = 40 A$, $I_{GT} = 60 \text{ mAdc}$)	t_{gt}	—	1.5	—	μs
Critical Rate-of-Rise of Off-State Voltage (Gate Open, $V_D = \text{Rated } V_{DRM}$, Exponential Waveform)	dv/dt	—	50	—	$V/\mu s$

1. Pulse Test: Pulse Width $\leq 300 \mu s$, Duty Cycle $\leq 2\%$.

FIGURE 1 — AVERAGE CURRENT DERATING

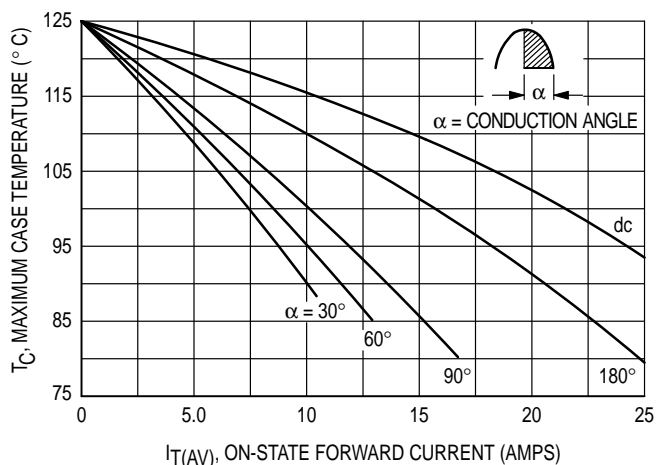


FIGURE 2 — MAXIMUM ON-STATE POWER DISSIPATION

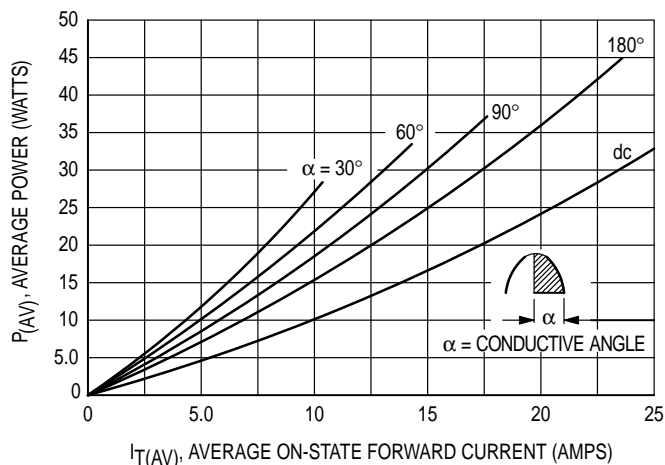


FIGURE 3 — GATE TRIGGER CURRENT

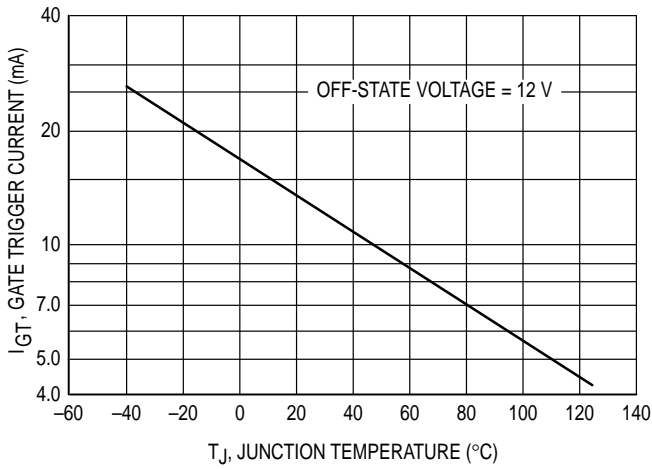


FIGURE 4 — NEW GATE TRIGGER VOLTAGE

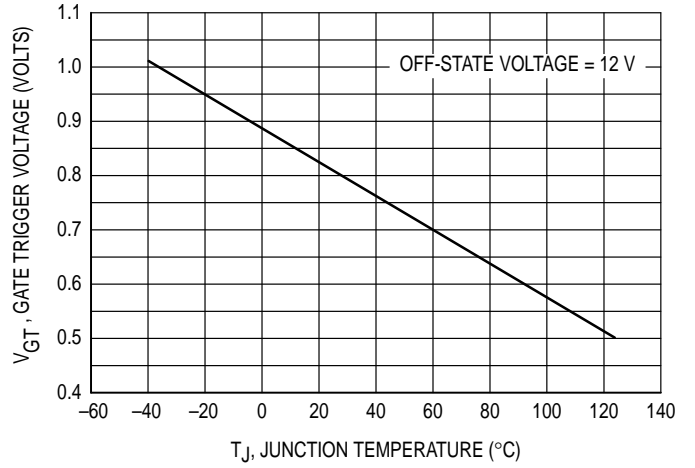


FIGURE 5 — HOLDING CURRENT

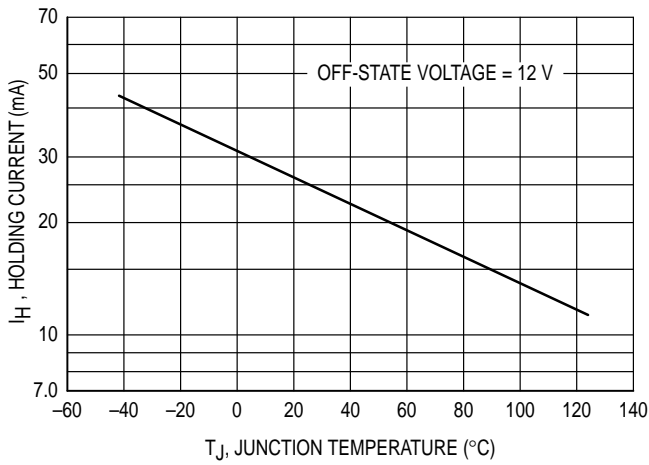


FIGURE 6 — TYPICAL FORWARD VOLTAGE

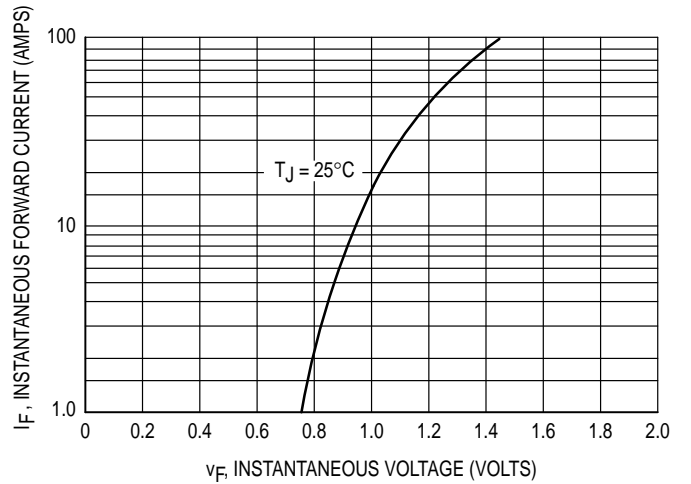
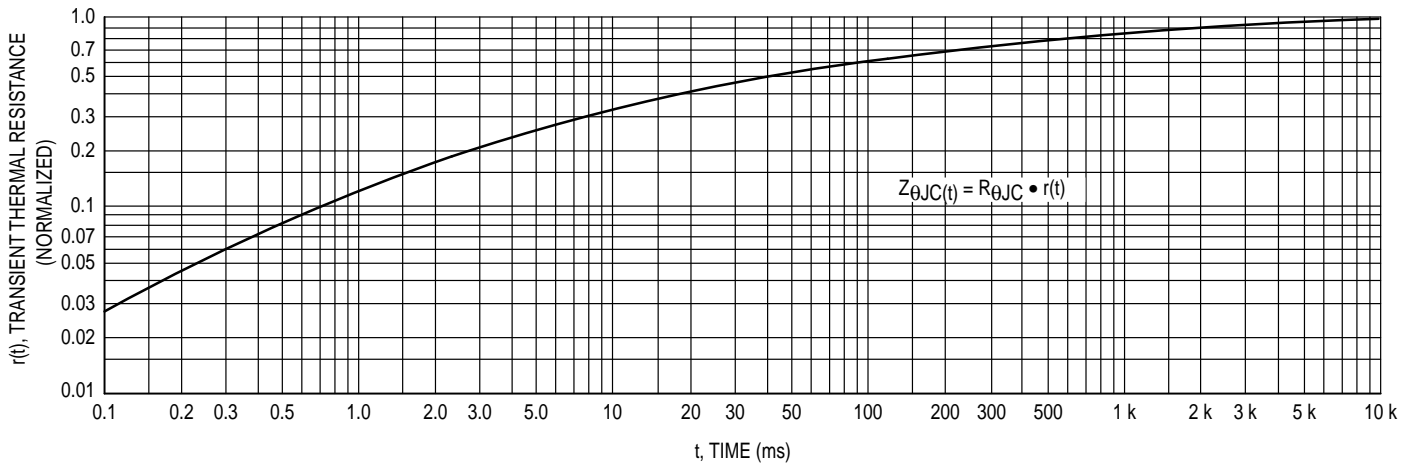
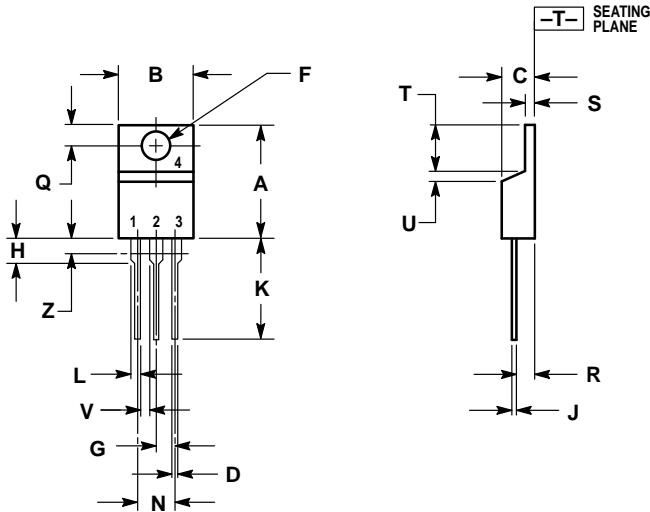


FIGURE 7 — THERMAL RESPONSE



PACKAGE DIMENSIONS



STYLE 3:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.014	0.022	0.36	0.55
K	0.500	0.562	12.70	14.27
L	0.045	0.055	1.15	1.39
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	—	1.15	—
Z	—	0.080	—	2.04

CASE 221A-04
(TO-220AB)

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